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Thin film deposition with time varying temperature

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We study the effects of time-dependent substrate/film temperature in the deposition of a mesoscopically thick film using a statistical model that accounts for diffusion of adsorbed atoms with coefficients dependent on an activation energy and temperature. For simplicity, a model where only adatoms without lateral neighbors can move is studied by computer simulation, with deposition of typically 10^4 atomic layers and temperature changes up to $30K$, near or below the room temperature range. Linearly varying and exponentially converging temperature cases are considered. If the temperature decreases during the growth, the global roughness slowly increases at short times, but may show a rapid growth with exponent $\beta > 1/2$ after $\sim 10^3$ monolayers. In the exponentially converging case, the local roughness shows evidence of anomalous scaling, with a large range of the anomalous exponent, and in the linearly decreasing case the local roughness may increase faster than a power law. If the temperature increases during the growth, a non-monotonic evolution of the global roughness may be observed, with a maximum in the linearly increasing case and a sequence of maximum and minimum in the case of exponential convergence to a final temperature. This is explained by the competition of kinetic roughening and the smoothing effect of increasing diffusion coefficients. If some of these features are observed in experiments, our results suggest to investigate the possibility of time varying temperature before relating them to more complex physico-chemical mechanisms.

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I. INTRODUCTION

The morphological properties of a growing film by vapor techniques are mainly determined by the balance between substrate/film temperature and pressure. High temperature helps the system to attain equilibrium states, for instance favoring formation of smooth surfaces in homoepitaxy, while the increase of pressure leads to faster adsorption and drives the system far from the equilibrium conditions [1]. For these reasons, many statistical models of thin film growth represent the competition of the external flux of atoms or molecules and temperature-dependent surface processes, such as diffusion, aggregation, and reactions [2–4]. They account for an external flux of atoms or molecules with rate F and for surface diffusion of aggregated species with coefficient D, so that the ratio $R \equiv D/F$ is the main parameter that represents the temperature/pressure interplay (possibly other activation energies are also model parameters) [3, 4].

The main quantity to characterize surface morphology is the roughness, which measures thickness fluctuations along the film surface. It may be measured for the whole surface (global roughness) or inside a box that glides over that surface (local roughness). The scaling properties with time and size are described by dynamic relations [3], which are called normal when local and global fluctuations scale with the same exponents [5] and anomalous when local and global exponents are different [6–10].

A question of experimental relevance is the effect of changing physico-chemical conditions during film growth. For example, a recent experimental work on electrodeposition of Prussian Blue films interpreted the growth as a process dominated by surface diffusion in which the time-increasing adsorption rate is responsible for an anomaly in the dynamic scaling relation [11]. The problem of spontaneous fluid imbibition in a porous medium is another system that shows anomalous scaling (AS) and is modeled as interface growth with time-dependent couplings [12].

This scenario motivated theoretical works on growth models where the microscopic rules of aggregation change in time. Ref. [13] showed that a sudden change in the parameters of the Edwards-Wilkinson (EW) equation [14] of interface growth may be responsible for nontrivial effects in roughness scaling, such as power-law relaxation to steady states. The possibility of AS was also discussed in the context of stochastic growth equations with time-dependent couplings and was illustrated for the EW equation with time-dependent surface tension in Ref. [15]. It showed good agreement with numerical results for models of spontaneous imbibition [16, 17]. In lattice models of film growth, a recent realization of AS was shown in competitive models with time-varying probabilities and involving uncorrelated deposition [18].

On the other hand, to our knowledge no work have already discussed the effects of time-varying conditions in realistic models of thin film deposition. For this reason,

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this paper is devoted to study a model of deposition and diffusion of adsorbed species in which the diffusion coefficients are affected by a time-dependent substrate/film temperature. For simplicity, the model assumes that only adatoms in terraces can move, while atoms with lateral neighbors are permanently aggregated. Despite its simplicity, the model shows several nontrivial effects on surface roughness scaling that may help to understand experimental results. In cases of decreasing temperature, there is evidence of AS for film thicknesses typical of real mesoscopically thick films, with rapidly increasing global roughness that suggests nontrivial growth exponents. In cases of increasing temperature, a non-monotonic evolution of the global roughness may be observed, possibly with a saturation for a wide range of film thickness. The main advance from previous works is to show those features in realistic conditions of film growth, since the model may be viewed an approximate description of low-temperature physical vapor deposition.

The rest of this paper is organized as follows. In Sec. II, we will define the model, review basic concepts of dynamic scaling of surface roughness, and discuss scaling properties for fixed temperature. In Sec. III, we will show numerical results for various conditions of decreasing temperature. In Sec. IV, we will show numerical results or various conditions of increasing temperature. In Sec. V, we summarize our results and present our conclusions.

II. BASIC DEFINITIONS AND CONCEPTS

A. Model definition

The model studied in this work was introduced in Ref. [19]. It is inspired in the Das Sarma and Tamborenea model of molecular beam epitaxy [20], but changed in order to allow a dynamic competition of deposition and diffusion, with the possibility of adatoms migrating to long distances in terraces. It also resembles the models of submonolayer growth with critical island size $i = 1$ [4], although here the deposition of a large number of layers is allowed.

The model is of solid-on-solid type, i. e. there is no overhang in the film surface. The deposit has a simple cubic lattice structure. The deposition begins with a flat substrate of linear size L in the xy plane, with the lattice parameter being the length unit. The deposit consequently has $L \times L$ columns and the column height is the z coordinate of the topmost adatom. There is an external flux of F atoms per site per unit time, measured in number of monolayers (ML) per second. An incident atom is adsorbed upon landing above a previously deposited atom or a substrate site. All adsorbed atoms with no lateral and no upper neighbor (i. e. isolated atoms in terraces) diffuse with coefficient D. If an adatom has a lateral or an upper neighbor, then it is permanently aggregated at that position. This is a reasonable assumption for low temperatures and reduces simulation times compared with models where all atoms are mobile. It has the disadvantage of not respecting detailed balance conditions, but various successful applications justify its use for submonolayer growth [4]. Fig. 1 illustrates the possible steps of some mobile atoms at the film surface.

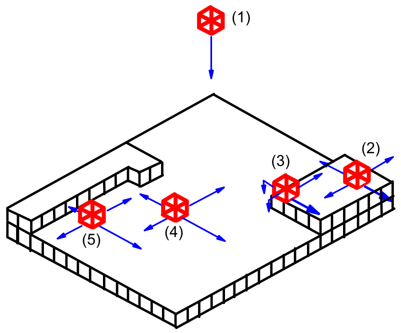

FIG. 1: Illustration of the model: deposition of an atom (1); adatom diffusion in terraces (2,4), with possibility of downhill movement and irreversible aggregation (3), and with possibility of irreversible aggregation at a step edge (5).

The diffusion coefficient D is expected to depend on temperature as $D = \nu_0 \exp\left(-E/k_B T\right)$, where ν_0 is a jump frequency and E is the activation energy in a flat surface, which typically amounts to tens of eV. The parameter $R \equiv D/F$ determines the film properties, since this is the average number of steps of a mobile adatom during the time of deposition of one layer of atoms (L^2 atoms). The other relevant parameter is the film thickness t, proportional to the deposition time. Our model allows downhill movement at terrace edges without additional energy barriers (Ehrlich-Schwebel) [21]. This movement always lead to permanent aggregation at the step edges. For this reason, the inverse process (uphill movement) is not possible. Our simulations are performed in lattices with $L = 512$. A fixed deposition parameter is $\nu_0/F = 10^{14}$ and the chosen activation energy value is $E = 0.6$ eV, which are close to estimates for Pd/Pd(100) submonolayer epitaxy [4, 22]. This cannot be taken as a direct application due to the different lattice structures. On the other hand, the physically important parameter is R, which is a function of E/T, thus choosing a fixed value of E and changing T does not restrict our conclusions. Since the model is suitable for low temperatures, we will consider temperature ranges in which R typically varies between 10^1 and 10^5. Additional reasons for this choice are presented in Sec. II C. In all cases, the temperature is uniform across the film.

During the simulation of a given sample, the adsorption of each new atom takes place in a time interval $1/\left(FL^2\right)$. After this process, R/L^2 steps of randomly chosen free atoms are performed. Since R/L^2 is usually not integer, and it may be small for large L, we keep its fractional part for determining the number of steps after the next adsorption events. If the temperature changes during the film growth, then the value of R is updated after the deposition of each complete layer (L^2 atoms), which corresponds to a unit time interval.

B. Dynamic scaling of surface roughness

The global roughness (or interface width) is defined as

$$W\left(L,t\right) \equiv \left\langle \overline{\left(h-\overline{h}\right)^2} \right\rangle^{1/2} , \tag{1}$$

where the overbars represent spatial averages and the angular brackets represent configurational averages over various samples. For short deposition times (small thicknesses), effects of the finite substrate size L are negligible and W scales as

$$W \sim t^{\beta}, \tag{2}$$

where β is called the growth exponent. For comparison with experimental data, the local roughness $w\left(r,t\right)$ is more useful. It is also defined as a root mean square height fluctuation, but the spatial average is limited to a box of size r, with $r<L$, and the configurational average is performed by gliding this box over the film surface and over various samples. In the regime of thin film growth (negligible effects of substrate size), it follows the Family-Vicsek (FV) dynamic scaling relation [5]

$$w\left(r,t\right) \approx A r^{\alpha_l} g\left(\frac{Bt}{r^z}\right). \tag{3}$$

Here, α_l is the local roughness exponent (sometimes called Hurst exponent), z is the dynamic exponent, B is a constant, and g is a scaling function such that $g(x)\sim 1$ for $x \gg 1$ (small box size) and $g(x) \sim x^{-\alpha_l/z}$ for $x \ll 1$ (large box size, where the local roughness coincides with the global one).

In systems with normal scaling, the amplitude A in Eq. (3) is a constant (time-independent), thus $\beta = \alpha_l/z$ and the global roughness exponent α equals the local one. A scaling analysis of $w\left(r,t\right)$ of several growth models in one- and two-dimensional substrates is presented in Ref. [23]. In systems with AS, the amplitude A scales as

$$A \sim t^{\kappa}, \tag{4}$$

with κ characterizing the degree of anomaly [8]. A FV relation can also be defined for the global roughness and involves the exponent α, but it is useful only if very long times / large thicknesses are attained.

C. Previous works

Here we restrict the discussion to results on two-dimensional substrates (growth in $2+1$ dimensions), which is the subject of the present work. Related full diffusion models were previously studied numerically with fixed temperature during the deposition. These models allowed diffusion of atoms with lateral neighbors, with an increase in the energy barrier proportional to the number of those neighbors. Some authors proposed that they had AS [24] or a logarithmic scaling of amplitude A in the FV relation [25]. Wilby et al [26] showed that the growth exponent β was close to value of the universality class of the fourth order nonlinear growth equation of Villain, Lai and Das Sarma (VLDS) [27, 28]. Recently, renormalization studies explained the long crossover to VLDS scaling [29, 30].

The model presented in Sec. II A was recently studied numerically, showing a FV relation for the global roughness that includes the R-dependence as [19]

$$W = \frac{L^{\alpha}}{R^{x}} f(R^y t/L^z), \tag{5}$$

with $\alpha \approx 2/3$, $z \approx 10/3$, $x \approx 0.5$, and $y \approx 1$. The exponents α and z agree with those of the VLDS class [3, 31, 32]. The values of exponents x and y were explained by scaling arguments [19].

For $R \geq 10^5$, the surface roughness of that model is very small even with very large thicknesses (10^4 or 10^5 ML) [19]. Thus, it is not in the regime of dynamic scaling. This is an additional reason for our simulations to be performed with relatively small values of R (for comparision, full diffusion models with values of R of the same order show larger values of the roughness, particularly if ES barriers are included [33]).

D. Scaling of local roughness

A recent work on numerical integration of the VLDS equation showed evidence of AS in $2+1$ dimensions [34], which raises the question on a possible AS in our lattice model. This feature was not investigated in Ref. [19], thus it is considered here.

We performed simulations of the model with $10 \leq R \leq 1000$ for fixed R (fixed temperature). Fig. 2 shows the local roughness as a function of box size for three values of that parameter. For $R=10$, there is a split in the curves for small r, which suggests AS. However, that split tends to disappear as the thickness increases. For instance, from $t=4000ML$ to $t=8000ML$, the change in the local roughness for $r=5$ is only 7%. For $R=100$ and $R=1000$, the split of the curves for different times is almost negligible for $t>10^3$. For those reasons, we understand that there is no asymptotic AS in our lattice model with fixed R, and an apparent anomaly appears only for small R and for small thicknesses due to some type of scaling correction.

Fig. 2 also shows that, for small r, the local roughness scales with local exponent $\alpha_l \approx 1/3$ [Eq. (3)], which is significantly below the VLDS value $\alpha_l = \alpha \approx 2/3$ [32]. This discrepancy is frequently observed in thin film

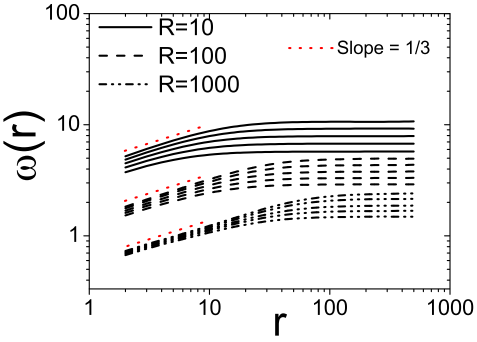

FIG. 2: Local roughness as a function of box size for R=10 (full line), R=100 (dashed line) and R=1000 (dashed dotted dotted line) at times $t = 500$ML, 1000ML, 2000ML, 4000ML and 8000ML, from bottom to top. The dotted line indicates the slope value of 1/3.

growth models due to scaling corrections, as explained in Ref. [23], and may not be viewed as a failure of the predicted model class.

III. DEPOSITION WITH DECREASING TEMPERATURE

These are situations with slow down of the diffusion process, thus roughening is facilitated. First we consider linearly decreasing temperature: (I) from $T_I = 300K$ to $T_F = 270K$ and (II) from $T_I = 270K$ to $T_F = 240K$, during the time interval for deposition of $t_{max} = 10^4 ML$, which is a reasonable thickness for mesoscopic films (T_I and T_F denote initial and final temperatures, respectively). Fig. 3a shows the time evolution of the parameter R and of the temperature, and Fig. 3b shows the evolution of the global roughness of the films. For small thicknesses ($t \leq 10^3 ML$), the slopes of the plots in Fig. 3b [effective exponents β; Eq. (2)] are close to or slightly below the VLDS value $\beta \approx 0.2$. This may be surprising because decreasing temperature favors roughness increase and was expected to provide a larger β. However, for case (I), the roughness is very small (typically smaller than unity), thus this is not a true scaling region where estimates of β can be reliably interpreted. For larger thicknesses, W rapidly increases in cases (I) and (II). For $5 \times 10^3 ML \leq t \leq 10^4 ML$, the effective exponents are $\beta \approx 0.70$ and $\beta \approx 0.82$, respectively. This nontrivial growth exponent cannot be interpreted by existing theories of interface growth which assume time-independent couplings.

Recall that $\beta = 1/2$ characterizes random uncorrelated deposition [3] and is expected when $R \to 0$. However, this not the case here: $R \sim 20$ at $T_F = 240K$ and $R \sim 700$ at $T_F = 270K$. Usual interpretations of $\beta > 1/2$ are preferential aggregation at surface hills instead of valleys, possibly with some surface instability, shadowing effects [35, 36], or Ehrlich-Schwebel barriers [21]. However, these features are also not present in our model. Moreover, large β is not related to large values of the roughness. For instance, very rough deposits produced by grain deposition models [37] have $\beta \sim 0.1$, which is well below the asymptotic value of the Kardar-Parisi-Zhang class [38].

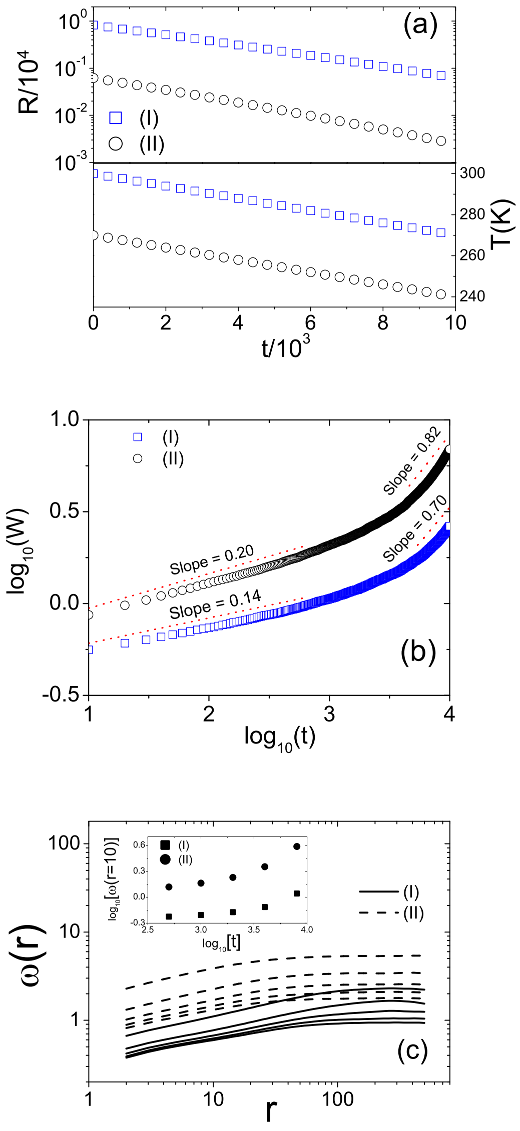

FIG. 3: (a) Parameter R as a function of the thickness, considering $E = 0.6$eV, $\nu_0/F = 10^{14}$, and temperature variation of cases (I) and (II). (b) Global roughness as a function of the thickness for cases (I) and (II). In (a) and (b), squares correspond to case (I) and circles to case (II). (c) Local roughness as a function of box size for cases (I) (solid lines) and (II) (dashed lines) at times $t = 500$ML, 1000ML, 2000ML, 4000ML and 8000ML, from bottom to top. The inset shows $\log_{10}(\omega)$ as a function of $\log_{10}(t)$ for $r = 10$.

The exponents $\beta > 1/2$ obtained here are a special consequence of the decreasing deposition temperature.

Thus, experimental works which find this result must consider the possibility that the temperature is changing during the deposition before choosing interpretations based on other microscopic mechanisms, such as those listed above. The possibility of time-increasing adsorption rates must also be considered because it also leads to time-decreasing R (this was the case in Ref. [11], where $\beta \approx 0.5$ was obtained). Fig. 3c shows the local roughness versus box size for some thicknesses in the range $500ML < t < 8000ML$. There is a significant split of the curves for small values of r, in contrast to the constant temperature case shown in Fig. 2 (note that vertical and horizontal scales are the same in Figs. 2 and 3c). It suggests AS, with the FV relation [Eq. (3)] having time-dependent amplitude A. However, for small and constant r, the scaling of A with time does not follow the power-law of Eq. (4) (see the inset of Fig. 3c); instead, A increases much faster in time. Again, if the slow down of surface diffusion is not accounted for, this result may naively suggest some sort of surface instability.

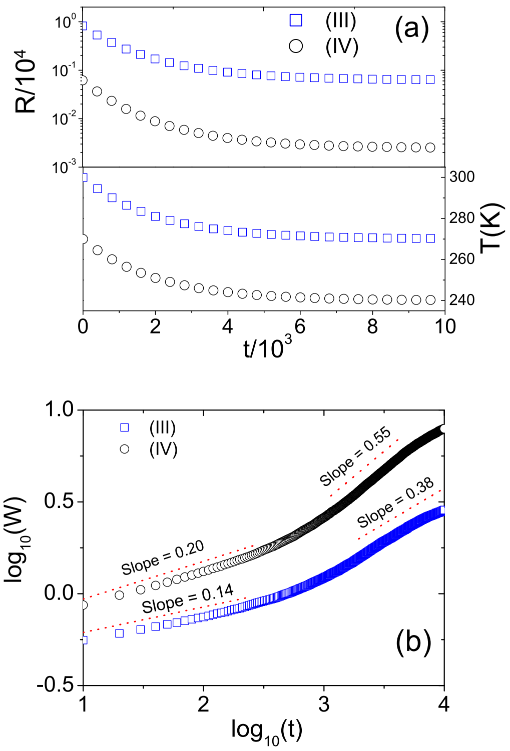

FIG. 4: (a) Parameter R as a function of the thickness, considering $E = 0.6$eV, $\nu_0/F = 10^{14}$, and temperature variation of cases (III) and (IV). (b) Global roughness as a function of the thickness for cases (III) and (IV). In all plots, squares correspond to case (III) and circles to case (IV).

Now we consider cases of exponential convergence of the temperature to a final value: (III) from $T_I = 300K$ to $T_F = 270K$ and (IV) from $T_I = 270K$ to $T_F = 240K$. In both cases, a characteristic time/thickness $t_c = 2000ML$ is chosen for the decay, so that:

$$T = T_F + (T_I - T_F) \exp\left(-t/t_c\right). \tag{6}$$

Deposition of $t = 10^4 ML = 5t_c$ layers is considered, thus the final temperatures of the films are very close to T_F. Cases (III) and (IV) represent systems exchanging heat by conduction with a colder reservoir (e. g. an initially heated system separated from the surroundings by a conducting material). Fig. 4a shows the time evolution of the parameter R and temperature in cases (III) and (IV). It contrasts with the linear decay in Fig. 3a because R rapidly decreases up to $t \sim t_c$, but decreases slowly during most of the deposition time, when the system attained a temperature close to the surroundings.Fig. 4b shows the evolution of the global roughness for cases (III) and (IV). Again, W increases slowly for small thicknesses and large effective exponents β are obtained for large thicknesses. In case (IV), where R decreases almost two orders of magnitude during the film growth, an exponent $\beta > 1/2$ is also found, which reinforces the conclusion that a careful interpretation of this result in real systems is necessary.

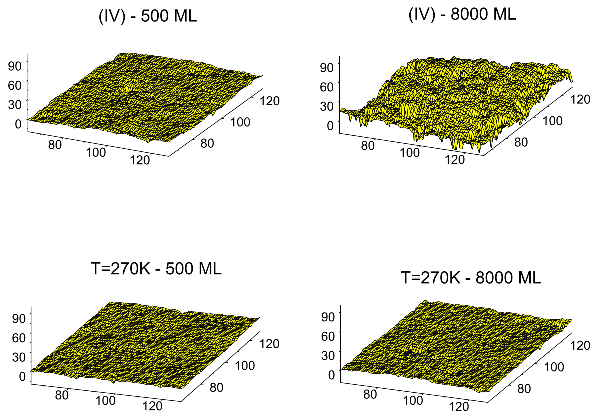

FIG. 5: Surface topography of films with thicknesses $t = 500$ML and $t = 8000$ML in (top) case (IV) and (bottom) with fixed temperature $T = 270$K.

Fig. 5 shows the surface topography of films with thicknesses $t = 500ML$ and $t = 8000ML$ in case (IV) and with fixed temperature $T = 270K$. While the films grown in fixed temperature are always smooth, a remarkable roughening is observed in the films grown with decreasing temperature, consistently with the large values of β.

Figs. 6a and 6b show the local roughness as a function of box size for cases (III) and (IV), respectively. Both plots show evidence of AS due to the split of the curves for small r. Surprisingly, this trend persists for thicknesses $t > 2t_c$, where the temperature is changing very slowly. Fig. 6c shows the scaling of $w(r = 10, t)$, which gives the anomaly exponents $\kappa = 0.28 \pm 0.01$ for case

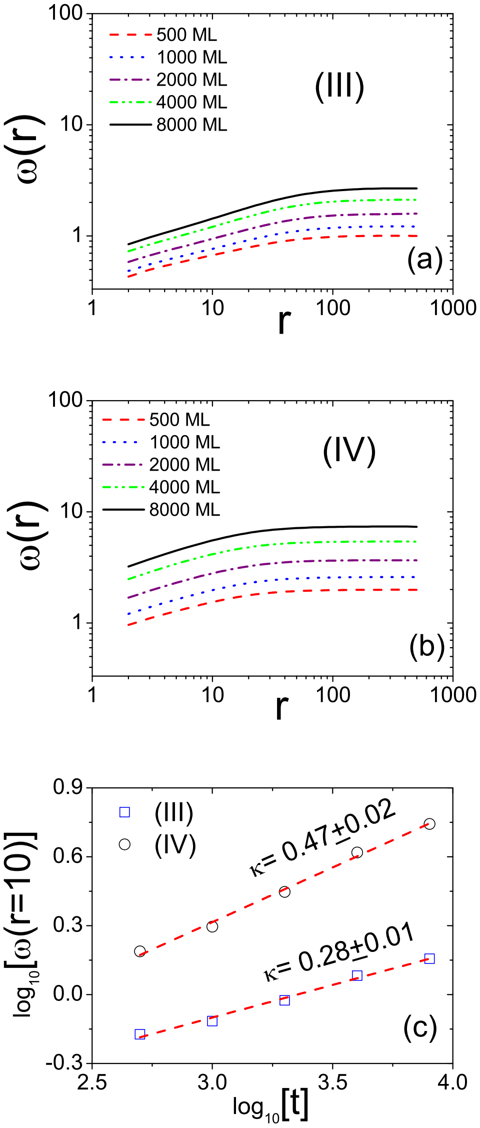

FIG. 6: (a), (b) Local roughness as a function of box size for cases (III) and (IV), respectively, at times $t = 500$ML, 1000ML, 2000ML, 4000ML and 8000ML, from bottom to top. (c) $\log_{10}(\omega)$ as a function of $\log_{10}(t)$ for $r = 10$ in cases (III) (squares) and (IV) (circles). The dashed lines indicate the linear fits for the κ evaluation. The corresponding values of κ are also shown.

(III) and $\kappa = 0.47 \pm 0.02$ for case (IV). This is AS found in conditions plausible in experimental work (note that maximal temperature changes are $30K$). It is important to stress that the AS found in cases (III) and (IV) is an apparent scaling restricted to the thickness range studied here. At long times, the deposit will attain the characteristic features of films grown with fixed T_F, which do not have AS, but have normal VLDS scaling. Cases (I) and (II), with linearly decreasing temperature, are necessarily limited to a finite time range, thus there is no asymptotic scaling. These features contrast with the true AS of the models in Ref. [18], although those models are not so close to real film growth. Finally, we observe that the local roughness exponents measured in Figs. 3c, 5a, and 5b are close to 1/3, similarly to the constant temperature case (Sec. II D).

IV. DEPOSITION WITH INCREASING TEMPERATURE

First we consider two cases of linearly increasing temperature: (V) from $T_I = 240K$ to $T_F = 270K$ and (VI) from $T_I = 270K$ to $T_F = 300K$, both from $t = 0$ to $t_{max} = 10^4 ML$. Fig. 7a shows the time evolution of the parameter R and of the temperature and Fig. 7b shows the evolution of the global roughness. The nontrivial result is the nonmonotonic variation of the roughness. It increases for short times due to spread of correlations and excitation of modes of increasing wavelength, as usual in kinetic roughening [3, 39]. However, it attains a maximum and begins to decrease due to the smoothing effect of large diffusion coefficients. The effect is more pronounced for smaller temperatures because the relative increase of R is larger.

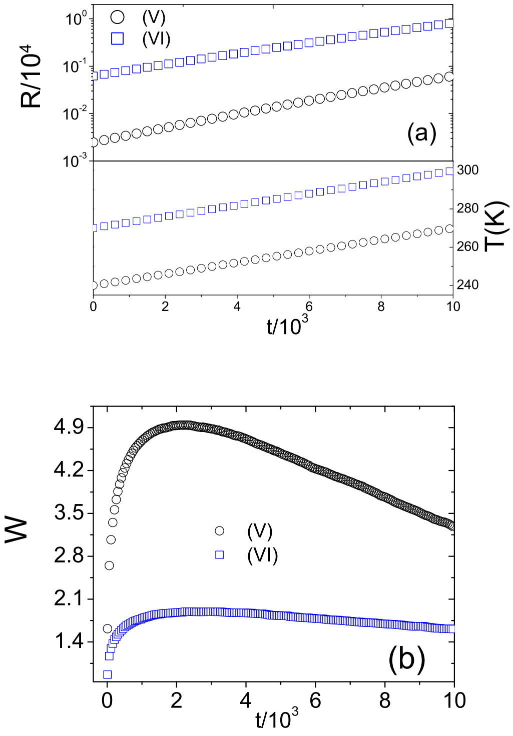

FIG. 7: (a) Parameter R as a function of the thickness, considering $E = 0.6$eV, $\nu_0/F = 10^{14}$, and temperature variation of cases (V) and (VI). (b) Global roughness as a function of the thickness for cases (V) and (VI). In all plots, circles correspond to case (V) and squares to case (VI).

The situation with exponential convergence of temperature [Eq. (6) with $T_I < T_F$] is more interesting, although the variations in W are smaller. We consider cases (VII) from $T_I = 240K$ to $T_F = 270K$ and (VIII) from $T_I = 270K$ to $T_F = 300K$, again from $t = 0$ to $t_{max} = 10^4 ML$, with characteristic decay time $t_c = 2000ML$. Fig. 8a shows the time evolution of the parameter R and of the temperature. Fig. 8b shows the evolution of the global roughness, which presents a maximum at small thicknesses for case (VII) and a plateau for case (VIII). These effects are similar to those of the linearly increasing T [(V) and (VI)]. However, for larger thicknesses, the roughness slowly increases. This is expected because the temperature slowly varies for $t > t_c$, thus the usual features of kinetic roughening (e. g. roughness increasing with time) are observed.

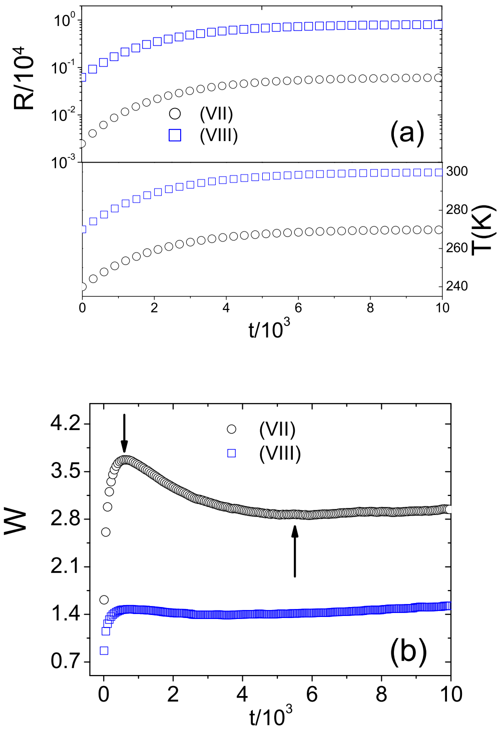

FIG. 8: (a) Parameter R as a function of the thickness, considering $E = 0.6$eV, $\nu_0/F = 10^{14}$, and temperature variation of cases (VII) and (VIII). (b) Global roughness as a function of the thickness for cases (VII) and (VIII). The arrows indicate a maximum and a minimum of global roughness. In all plots, circles correspond to case (VII) and squares to case (VIII).

The presence of two extremal values in the roughness (a maximum and a minimum) was already shown in an electrodeposition model where the time-dependent adsorption rate had a maximum [40]. This corresponds to a minimum of an effective diffusion-to-deposition rate R for that model. The increase of R after that minimum seems to be responsible for the effect of reducing the roughness in a certain time window, similarly to our model. The deposition with large R may also lead to roughness oscillations at short times due to fluctuations between partial and complete filling of the first atomic layers. This feature was shown by Pal and Landau [41, 42] in some lattice models and has no relation with the roughness evolution presented here. Indeed, those oscillations disappear after deposition of approximately 10 layers (maybe less), in contrast to our models.

V. CONCLUSIONS

We studied a thin film growth model in which the surface diffusion coefficients of adsorbed species are related to the substrate/film temperature in conditions where that temperature increases or decreases during the deposition. The model assumes that only adatoms in terraces can move and was formerly studied only in the case of constant deposition temperature.

In all cases analyzed here, 10^4 atomic layers were grown with temperatures in the range of room temperature or below and variations during the growth up to $30K$, which are feasible conditions with many experimental techniques. Cases of temperature varying linearly in time and of an exponential convergence to a final temperature were separately analyzed, the later representing systems exchanging heat by conduction with a thermal reservoir. If the temperature decreases during the growth, the global roughness slowly increases at short times but eventually turns to be a rapidly increasing function of time. In several cases, growth exponents $\beta > 1/2$ are obtained in the thickness range $10^3 ML < t < 10^4 ML$. This shows that the simple physical mechanism of reducing the temperature during the growth may lead to nontrivial exponents which are usually related to more complicated features, such as step energy barriers or other mechanisms that generate instabilities. Moreover, the local roughness shows evidence of anomalous scaling in the thickness range analyzed. In the cases of exponential convergence to a final temperature, several values of the anomaly exponent may be obtained in the thickness range analyzed. In the cases of linear temperature decrease, the local roughness in a small box size may increase in time even faster than a power law.

If the temperature increases during the growth, a nonmonotonic evolution of the global roughness may be observed. In cases of linear temperature increase, a maximum of roughness is usually observed, being more pronounced for lower temperature ranges. In the case of exponentially converging temperature, a maximum and a minimum may be observed (eventually turning into a plateau in the $logW \times \log t$ plot). These features are interpreted as a consequence of competition of kinetic roughening, which leads to roughness increase, and the smoothing effect of increasing diffusion coefficients.

Stochastic growth equation approaches [15] and lattice models [18] have already considered the effect of time-varying couplings in interface growth, with emphasis on anomalous scaling properties. The main advance of the present work is to show that a series of nontrivial features of surface roughness scaling (including anomalous scaling) appear in realistic conditions of film growth. We expect that our results may be helpful for the interpretation of previous or future works on thin film deposition in which the temperature may vary during that process.

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